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February 2016



# FOD3120 High Noise Immunity, 2.5 A Output Current, Gate Drive Optocoupler

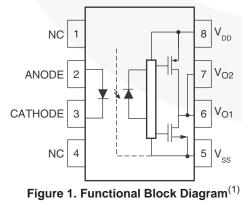
## Features

- High Noise Immunity Characterized by 35 kV/µs Minimum Common Mode Rejection
- 2.5 A Peak Output Current Driving Capability for Most 1200 V/20 A IGBT
- Use of P-channel MOSFETs at Output Stage Enables Output Voltage Swing Close to The Supply Rail
- Wide Supply Voltage Range from 15 V to 30 V
- Fast Switching Speed
  - 400 ns max. Propagation Delay
  - 100 ns max. Pulse Width Distortion
- Under Voltage LockOut (UVLO) with Hysteresis
- Extended Industrial Temperate Range, -40°C to 100°C Temperature Range
- Safety and Regulatory Approved
  UL1577, 5000 V<sub>RMS</sub> for 1 min.
  - DIN EN/IEC60747-5-5
- R<sub>DS(ON)</sub> of 1 Ω (typ.) Offers Lower Power Dissipation
- >8.0 mm Clearance and Creepage Distance (Option 'T' or 'TS')
- 1,414 V Peak Working Insulation Voltage (VIORM)

# Applications

- Industrial Inverter
- Uninterruptible Power Supply
- Induction Heating
- Isolated IGBT/Power MOSFET Gate Drive

## **Functional Block Diagram**



#### Note:

1. 0.1  $\mu$ F bypass capacitor must be connected between pins 5 and 8.

## Description

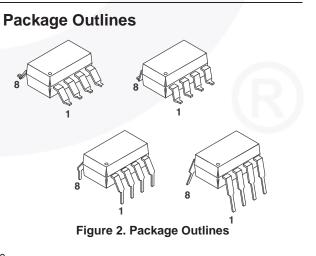
The FOD3120 is a 2.5 A Output Current Gate Drive Optocoupler, capable of driving most medium power IGBT/MOSFET. It is ideally suited for fast switching driving of power IGBT and MOSFETs used in motor control inverter applications, and high performance power system.

It utilizes Fairchild's coplanar packaging technology, Optoplanar<sup>®</sup>, and optimized IC design to achieve high noise immunity, characterized by high common mode rejection.

It consists of a gallium aluminum arsenide (AlGaAs) light emitting diode optically coupled to an integrated circuit with a high-speed driver for push-pull MOSFET output stage.

### **Related Resources**

- FOD3150, 1 A Output Current, Gate Drive Optocoupler Datasheet
- www.fairchildsemi.com/products/optoelectronics/



## **Truth Table**

LED	V <sub>DD</sub> -V <sub>SS</sub> "Positive Going" (Turn-on)	V <sub>DD</sub> -V <sub>SS</sub> "Negative Going" (Turn-off)	v <sub>o</sub>
Off	0 V to 30 V	0 V to 30 V	Low
On	0 V to 11.5 V	0 V to 10 V	Low
On	11.5 V to 13.5 V	10 V to 12 V	Transition
On	13.5 V to 30 V	12 V to 30 V	High

# **Pin Definitions**

Pin #	Name	Description
1	NC	Not Connected
2	Anode	LED Anode
3	Cathode	LED Cathode
4	NC	Not Connected
5	V <sub>SS</sub>	Negative Supply Voltage
6	V <sub>O2</sub>	Output Voltage 2 (internally connected to V <sub>O1</sub> )
7	V <sub>O1</sub>	Output Voltage 1
8	V <sub>DD</sub>	Positive Supply Voltage

# ©2 FC

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OD3120 Rev. 1.4	

#### www.fairchildsemi.com

## Safety and Insulation Ratings

As per DIN EN/IEC 60747-5-5, this optocoupler is suitable for "safe electrical insulation" only within the safety limit data. Compliance with the safety ratings shall be ensured by means of protective circuits.

Parameter	Characteristics	
	< 150 V <sub>RMS</sub>	I–IV
Installation Classifications per DIN VDE 0110/1.89 Table 1, For Rated Mains Voltage	< 300 V <sub>RMS</sub>	I–IV
	< 450 V <sub>RMS</sub>	I–III
	< 600 V <sub>RMS</sub>	I–III
	< 1000 V <sub>RMS</sub> (Option T, TS)	I–III
Climatic Classification		40/100/21
Pollution Degree (DIN VDE 0110/1.89)		2
Comparative Tracking Index		175

Symbol	Parameter	Value	Unit
M	Input-to-Output Test Voltage, Method A, $V_{IORM} \times 1.6 = V_{PR}$ , Type and Sample Test with $t_m = 10$ s, Partial Discharge < 5 pC	2,262	V <sub>peak</sub>
V <sub>PR</sub>	Input-to-Output Test Voltage, Method B, $V_{IORM} \times 1.875 = V_{PR}$ , 100% Production Test with $t_m = 1 \text{ s}$ , Partial Discharge < 5 pC	2,651	V <sub>peak</sub>
VIORM	Maximum Working Insulation Voltage	1,414	V <sub>peak</sub>
V <sub>IOTM</sub>	Highest Allowable Over-Voltage	6,000	V <sub>peak</sub>
	External Creepage	≥ 8.0	mm
	External Clearance	≥ 7.4	mm
	External Clearance (for Option T or TS, 0.4" Lead Spacing)	≥ 10.16	mm
DTI	Distance Through Insulation (Insulation Thickness)	≥ 0.5	mm
Τ <sub>S</sub>	Case Temperature <sup>(2)</sup>	175	°C
I <sub>S,INPUT</sub>	Input Current <sup>(2)</sup>	400	mA
P <sub>S,OUTPUT</sub>	Output Power (Duty Factor $\leq 2.7\%$ ) <sup>(2)</sup>	700	mW
R <sub>IO</sub>	Insulation Resistance at $T_S$ , $V_{IO}$ = 500 $V^{(2)}$	> 10 <sup>9</sup>	Ω

#### Note:

2. Safety limit value - maximum values allowed in the event of a failure.

### Absolute Maximum Ratings (T<sub>A</sub> = 25°C unless otherwise specified)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Paramete	er	Value	Unit
T <sub>STG</sub>	Storage Temperature		-55 to +125	°C
T <sub>OPR</sub>	Operating Temperature		-40 to +100	°C
TJ	Junction Temperature		-40 to +125	°C
T <sub>SOL</sub>	Lead Wave Solder Temperature (refer to page 21 for reflow solder	profile)	260 for 10sec	°C
I <sub>F(AVG)</sub>	Average Input Current		25	mA
I <sub>F(PEAK)</sub>	Peak Transient Forward Current <sup>(3</sup>	3)	1	А
f	Operating Frequency <sup>(4)</sup>		50	kHz
V <sub>R</sub>	Reverse Input Voltage		5	V
I <sub>O(PEAK)</sub>	Peak Output Current <sup>(5)</sup>		3.0	А
	Supply Voltage		0 to 35	V
$V_{DD} - V_{SS}$	Supply Voltage	$T_A \ge 90^{\circ}C$	0 to 30	v
V <sub>O(PEAK)</sub>	Peak Output Voltage		0 to V <sub>DD</sub>	V
t <sub>R(IN)</sub> , t <sub>F(IN)</sub>	Input Signal Rise and Fall Time		500	ns
PDI	Input Power Dissipation <sup>(6)(8)</sup>		45	mW
PD <sub>O</sub>	Output Power Dissipation <sup>(7)(8)</sup>		250	mW

#### Notes:

3. Pulse Width,  $P_W \leq 1~\mu s,\,300~pps$ 

- 4. Exponential Waveform,  $I_{O(PEAK)} \le | 2.5 \text{ A} | (\le 0.3 \text{ } \mu\text{s})$
- 5. Maximum pulse width = 10 µs, maximum duty cycle = 1.1%
- 6. Derate linearly above 87°C, free air temperature at a rate of 0.77 mW/°C
- 7. No derating required across temperature range.
- 8. Functional operation under these conditions is not implied. Permanent damage may occur if the device is subjected to conditions outside these ratings.

### **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Value	Unit
T <sub>A</sub>	Ambient Operating Temperature	-40 to +100	°C
$V_{DD} - V_{SS}$	Power Supply	15 to 30	V
I <sub>F(ON)</sub>	Input Current (ON)	7 to 16	mA
V <sub>F(OFF)</sub>	Input Voltage (OFF)	0 to 0.8	V

## **Isolation Characteristics**

Apply over all recommended conditions, typical value is measured at  $T_A = 25^{\circ}C$ 

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
V <sub>ISO</sub>	Input-Output Isolation Voltage	$ \begin{array}{l} T_{A} = 25^{\circ}C, \ R.H. < 50\%, \ t = 1.0min, \\ I_{I-O} \leq 10 \ \mu A, \ 50 \ Hz^{(9)(10)} \end{array} $	5,000			V <sub>RMS</sub>
R <sub>ISO</sub>	Isolation Resistance	$V_{I-O} = 500 V^{(9)}$		10 <sup>11</sup>		Ω
C <sub>ISO</sub>	Isolation Capacitance	$V_{I-O} = 0 V$ , Freq = 1.0 MHz <sup>(9)</sup>		1		pF

#### Notes:

9. Device is considered a two terminal device: Pins 2 and 3 are shorted together and Pins 5, 6, 7 and 8 are shorted together.

10. 5,000  $V_{RMS}$  for 1 minute duration is equivalent to 6,000 VAC<sub>RMS</sub> for 1 second duration.

## **Electrical Characteristics**

Apply over all recommended conditions, typical value is measured at  $V_{DD}$  = 30 V,  $V_{SS}$  = Ground,  $T_A$  = 25°C unless otherwise specified.

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit	
V <sub>F</sub>	Input Forward Voltage	I <sub>F</sub> = 10 mA	1.2	1.5	1.8	V	
$\Delta(V_{F} / T_{A})$	Temperature Coefficient of Forward Voltage			-1.8		mV/ºC	
BV <sub>R</sub>	Input Reverse Breakdown Voltage	I <sub>R</sub> = 10 μA	5			V	
C <sub>IN</sub>	Input Capacitance	f = 1 MHz, V <sub>F</sub> = 0V		60		pF	
1	High Level Output	V <sub>O</sub> = V <sub>DD</sub> – 3 V	-1.0	-2.0	-2.5	А	
I <sub>OH</sub>	Current <sup>(4)</sup>	$V_{O} = V_{DD} - 6 V$	-2.0		-2.5		
	Low Level Output	V <sub>O</sub> = V <sub>SS</sub> + 3 V	1.0	2.0	2.5	А	
I <sub>OL</sub>	Current <sup>(4)</sup>	$V_{O} = V_{SS} + 6 V$	2.0		2.5		
M	High Level Output Voltage	I <sub>F</sub> = 10 mA, I <sub>O</sub> = -2.5 A	V <sub>DD</sub> – 6.25 V	$V_{DD} - 2.5 V$		v	
V <sub>OH</sub>		I <sub>F</sub> = 10 mA, I <sub>O</sub> = -100 mA	$V_{DD} - 0.25 V$	V <sub>DD</sub> – 0.1 V		v	
M	Low Level Output Voltage	I <sub>F</sub> = 0 mA, I <sub>O</sub> = 2.5 A		V <sub>SS</sub> + 2.5 V	V <sub>SS</sub> + 6.25 V	v	
V <sub>OL</sub>		I <sub>F</sub> = 0 mA, I <sub>O</sub> = 100 mA		$V_{SS}$ + 0.1 V	$V_{SS}$ + 0.25 V	V	
I <sub>DDH</sub>	High Level Supply Current	V <sub>O</sub> = Open, I <sub>F</sub> = 7 to 16 mA		2.8	3.8	mA	
I <sub>DDL</sub>	Low Level Supply Current	V <sub>O</sub> = Open, V <sub>F</sub> = 0 to 0.8 V		2.8	3.8	mA	
I <sub>FLH</sub>	Threshold Input Current Low to High	I <sub>O</sub> = 0 mA, V <sub>O</sub> > 5 V		2.3	5.0	mA	
V <sub>FHL</sub>	Threshold Input Voltage High to Low	I <sub>O</sub> = 0 mA, V <sub>O</sub> < 5 V	0.8			V	
V <sub>UVLO+</sub>	Under Voltage Lockout	I <sub>F</sub> = 10 mA, V <sub>O</sub> > 5 V	11.5	12.7	13.5	V	
V <sub>UVLO</sub>	Threshold	I <sub>F</sub> = 10 mA, V <sub>O</sub> < 5 V	10.0	11.2	12.0	V	
UVLO <sub>HYS</sub>	Under Voltage Lockout Threshold Hysteresis			1.5		V	

## **Switching Characteristics**

Apply over all recommended conditions, typical value is measured at  $V_{DD}$  = 30 V,  $V_{SS}$  = Ground,  $T_A$  = 25°C unless otherwise specified.

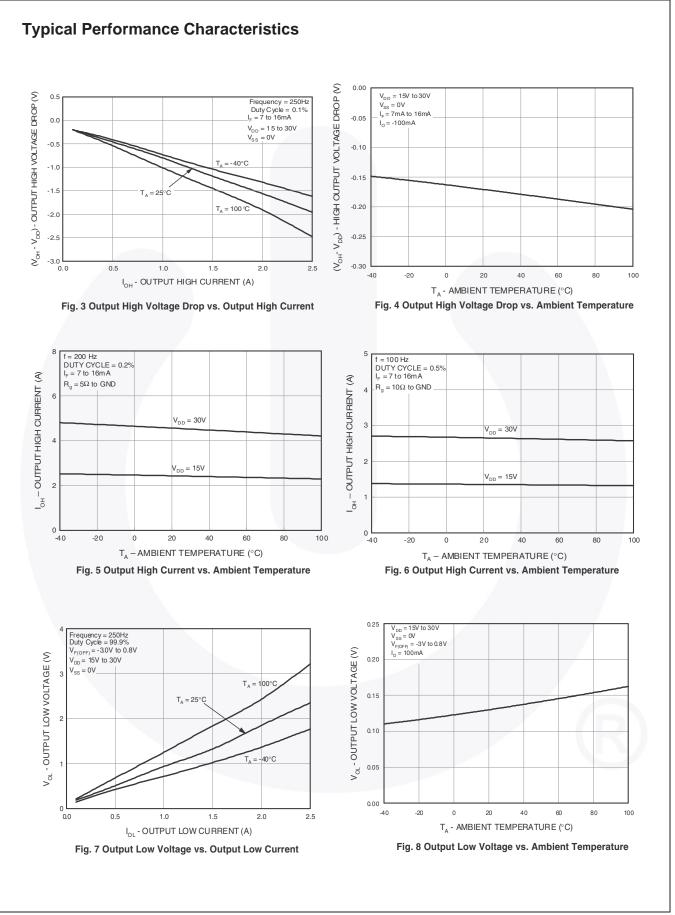
Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
t <sub>PHL</sub>	Propagation Delay Time to Logic Low Output		150	275	400	ns
t <sub>PLH</sub>	Propagation Delay Time to Logic High Output		150	255	400	ns
PWD	Pulse Width Distortion,   t <sub>PHL</sub> – t <sub>PLH</sub>	I <sub>F</sub> = 7 mA to 16 mA, Rg = 10 Ω , Cg =10 nF,		20	100	ns
PDD (Skew)	Propagation Delay Difference Between Any Two Parts or Channels, $(t_{PHL} - t_{PLH})^{(11)}$	f = 10 kHz, Duty Cycle = 50%	-250		250	ns
t <sub>R</sub>	Output Rise Time (10% – 90%)			60		ns
t <sub>F</sub>	Output Fall Time (90% – 10%)			60		ns
t <sub>UVLO ON</sub>	UVLO Turn On Delay	I <sub>F</sub> = 10 mA, V <sub>O</sub> > 5 V		1.6		μs
t <sub>UVLO OFF</sub>	UVLO Turn Off Delay	I <sub>F</sub> = 10 mA, V <sub>O</sub> < 5 V		0.4		μs
CM <sub>H</sub>	Common Mode Transient Immunity at Output High	$T_A = 25^{\circ}C, V_{DD} = 30 V,$ $I_F = 7 \text{ to } 16 \text{ mA},$ $V_{CM} = 2000 V^{(12)}$	35	50		kV/µs
CM <sub>L</sub>	Common Mode Transient Immunity at Output Low	$T_A = 25^{\circ}C, V_{DD} = 30 V, V_F = 0 V,$ $V_{CM} = 2000 V^{(13)}$	35	50		kV/µs

#### Notes:

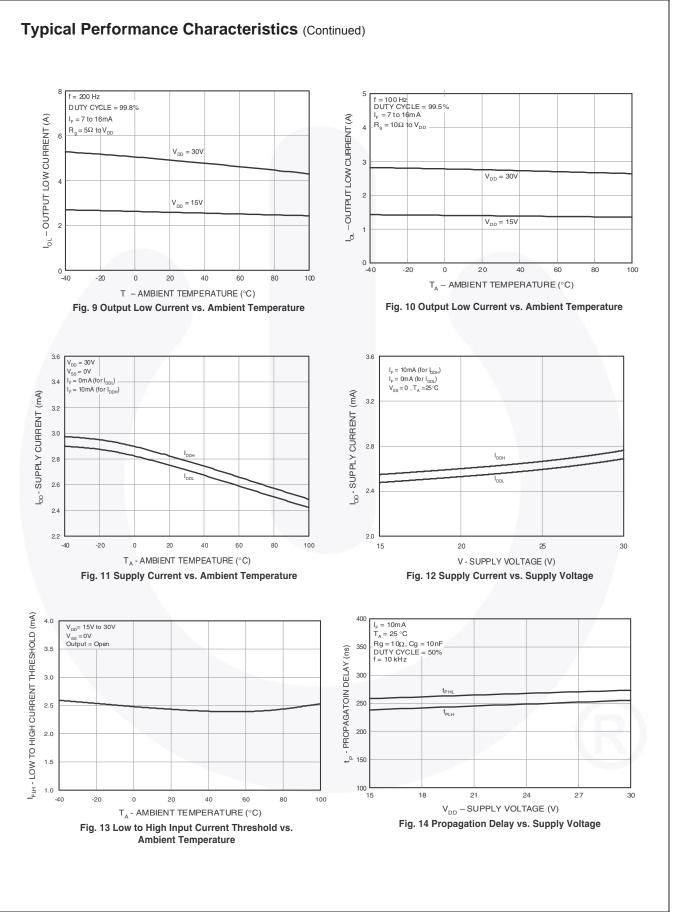
11. The difference between t<sub>PHL</sub> and t<sub>PLH</sub> between any two FOD3120 parts under same test conditions.

 Common mode transient immunity at output high is the maximum tolerable negative dVcm/dt on the trailing edge of the common mode impulse signal, Vcm, to assure that the output will remain high (i.e. V<sub>O</sub> > 15.0 V).

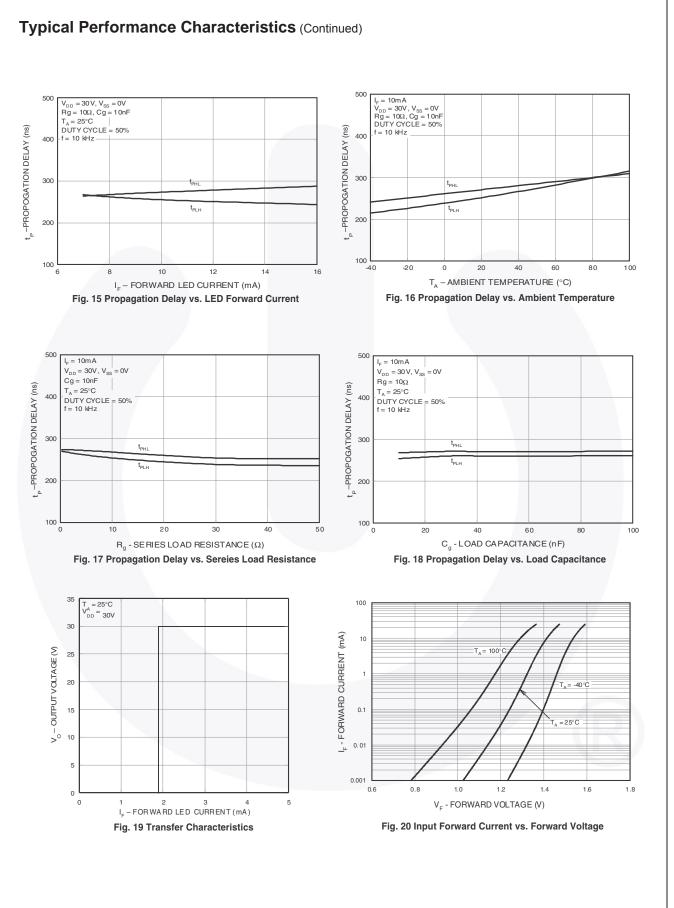
 Common mode transient immunity at output low is the maximum tolerable positive dVcm/dt on the leading edge of the common pulse signal, Vcm, to assure that the output will remain low (i.e. V<sub>O</sub> < 1.0 V).</li>

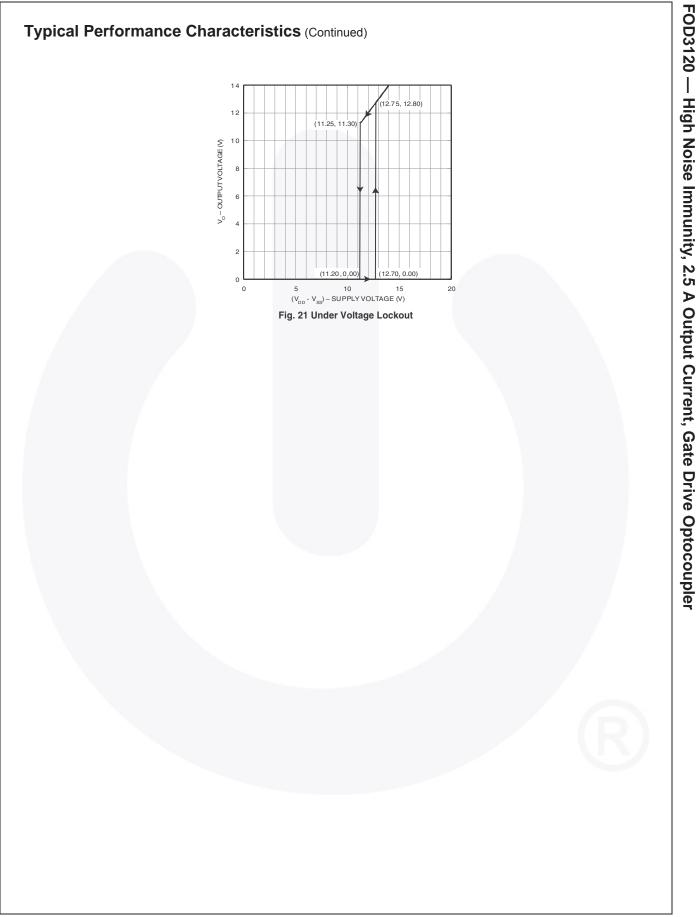


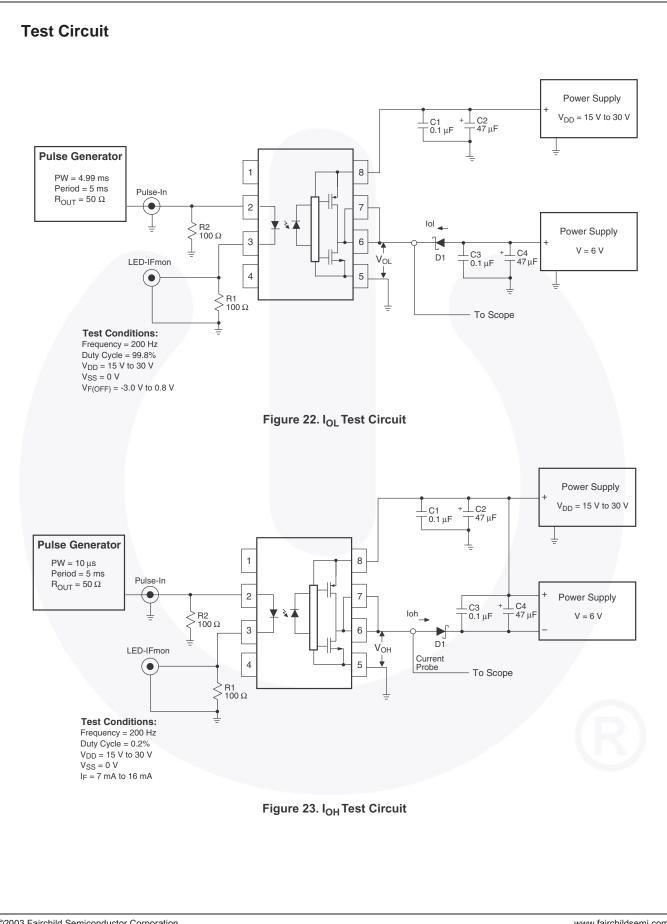
FOD3120 — High Noise Immunity, 2.5 A Output Current, Gate Drive Optocoupler



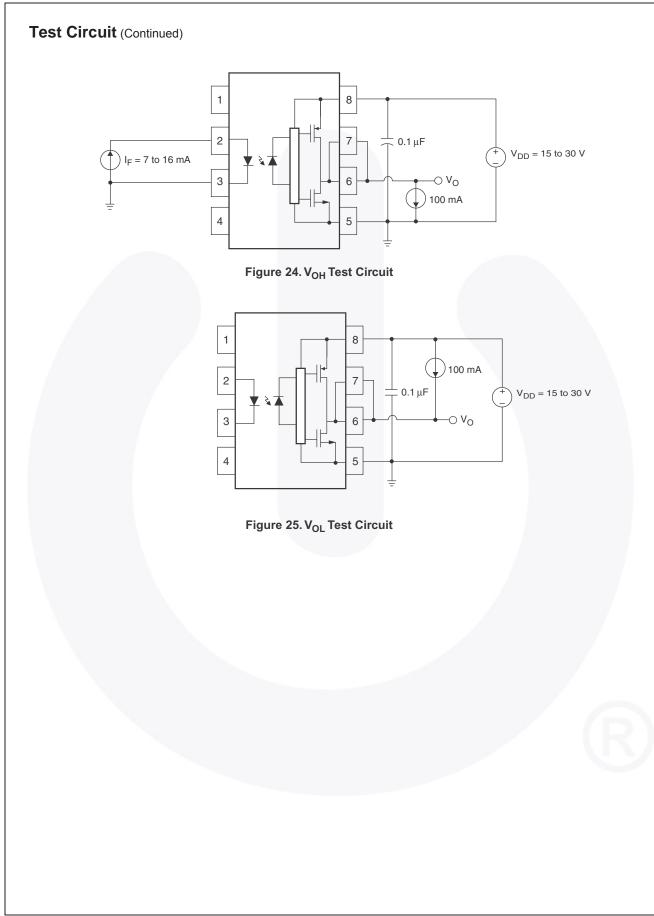
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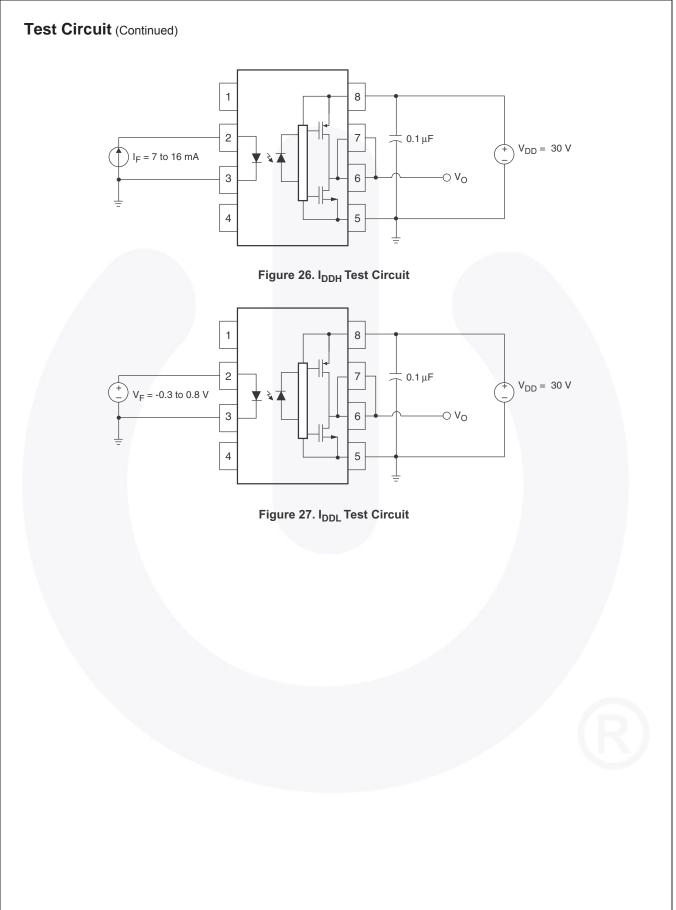




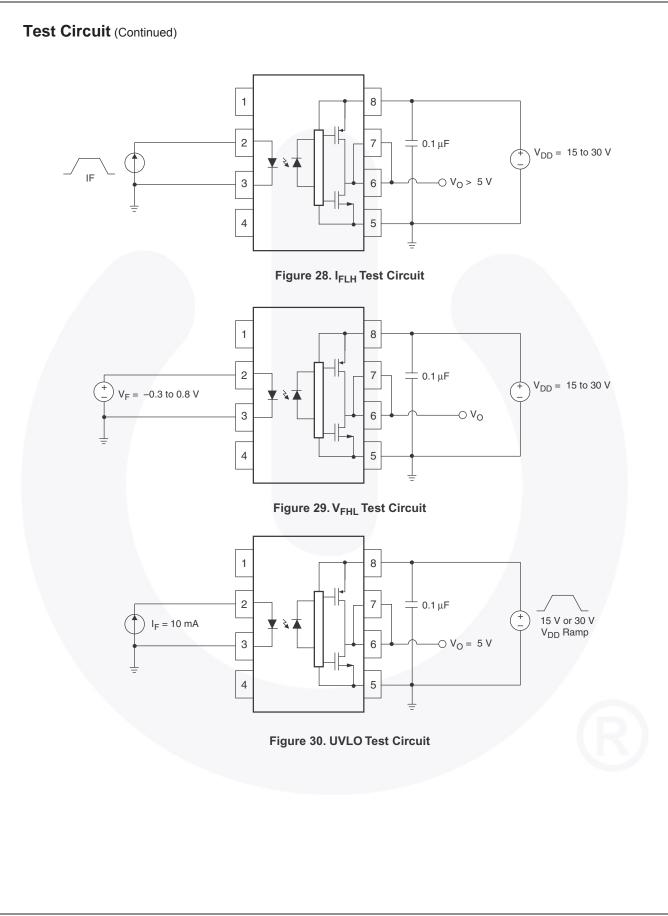


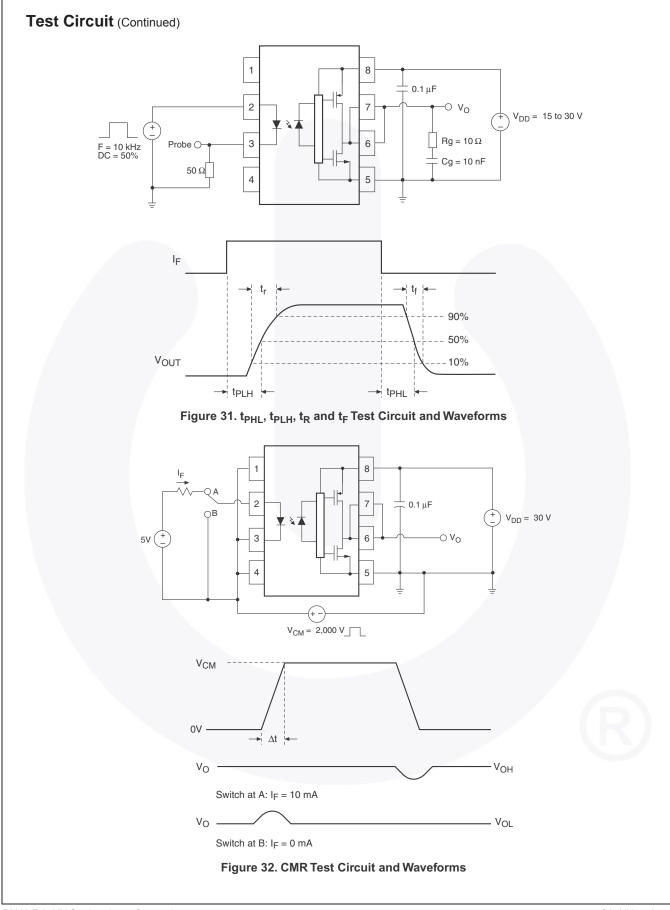
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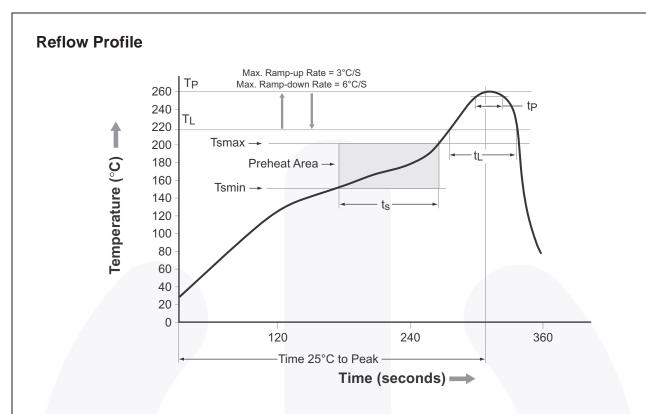




FOD3120 — High Noise Immunity, 2.5 A Output Current, Gate Drive Optocoupler







Profile Freature	Pb-Free Assembly Profile		
Temperature Min. (Tsmin)	150°C		
Temperature Max. (Tsmax)	200°C		
Time (t <sub>S</sub> ) from (Tsmin to Tsmax)	60–120 seconds		
Ramp-up Rate (t <sub>L</sub> to t <sub>P</sub> )	3°C/second max.		
Liquidous Temperature (T <sub>L</sub> )	217°C		
Time (t <sub>L</sub> ) Maintained Above (T <sub>L</sub> )	60–150 seconds		
Peak Body Package Temperature	260°C +0°C / –5°C		
Time (t <sub>P</sub> ) within 5°C of 260°C	30 seconds		
Ramp-down Rate (T <sub>P</sub> to T <sub>L</sub> )	6°C/second max.		
Time 25°C to Peak Temperature	8 minutes max.		

## **Ordering Information**

Part Number	Package	Packing Method
FOD3120	DIP 8-Pin	Tube (50 units per tube)
FOD3120S	SMT 8-Pin (Lead Bend)	Tube (50 units per tube)
FOD3120SD	SMT 8-Pin (Lead Bend)	Tape and Reel (1,000 units per reel)
FOD3120V	DIP 8-Pin, DIN_EN/IEC60747-5-5 option	Tube (50 units per tube)
FOD3120SV	SMT 8-Pin (Lead Bend), DIN_EN/IEC60747-5-5 option	Tube (50 units per tube)
FOD3120SDV	SMT 8-Pin (Lead Bend), DIN_EN/IEC60747-5-5 option	Tape and Reel (1,000 units per reel)
FOD3120TV	DIP 8-Pin, 0.4" Lead Spacing, DIN_EN/IEC60747-5-5 option	Tube (50 units per tube)
FOD3120TSV	SMT 8-Pin, 0.4" Lead Spacing, DIN_EN/IEC60747-5-5 option	Tube (50 units per tube)
FOD3120TSR2V	SMT 8-Pin, 0.4" Lead Spacing, DIN_EN/IEC60747-5-5 option	Tape and Reel (700 units per reel)

# **Marking Information**

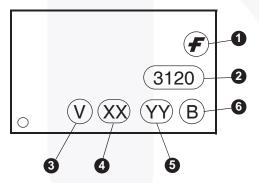
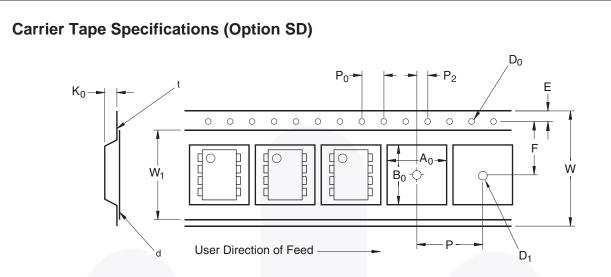
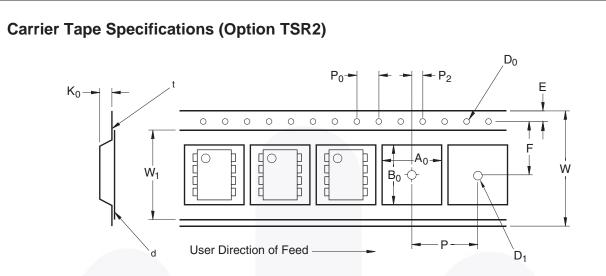


Figure 33. Top Mark

Definitions			
1	Fairchild logo		
2	Device number		
3	DIN_EN/IEC60747-5-5 Option (only appears on component ordered with this option)		
4	Two digit year code, e.g., '16'		
5	Two digit work week ranging from '01' to '53'		
6	Assembly package code		

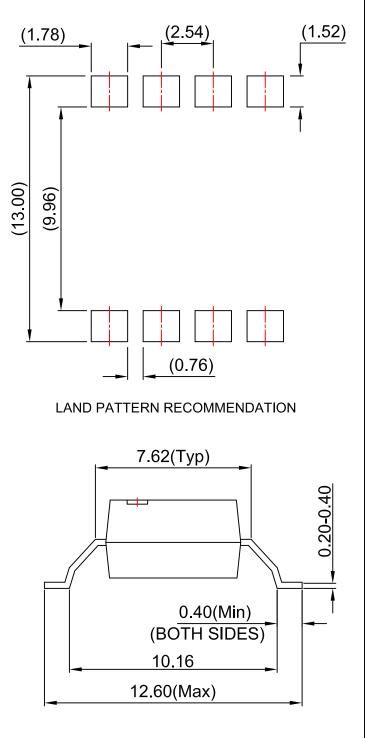


Symbol	Description	Dimension in mm
W	Tape Width	16.0 ± 0.3
t	Tape Thickness	0.30 ± 0.05
P <sub>0</sub>	Sprocket Hole Pitch	4.0 ± 0.1
D <sub>0</sub>	Sprocket Hole Diameter	1.55 ± 0.05
E	Sprocket Hole Location	1.75 ± 0.10
F	Pocket Location	7.5 ± 0.1
P <sub>2</sub>		2.0 ± 0.1
Р	Pocket Pitch	12.0 ± 0.1
A <sub>0</sub>	Pocket Dimensions	10.30 ±0.20
B <sub>0</sub>		10.30 ±0.20
K <sub>0</sub>		4.90 ±0.20
W <sub>1</sub>	Cover Tape Width	13.2 ± 0.2
d	Cover Tape Thickness	0.1 max
	Max. Component Rotation or Tilt	10°
R	Min. Bending Radius	30



Symbol	Description	Dimension in mm	
W	Tape Width	24.0 ± 0.3	
t	Tape Thickness	0.40 ± 0.1	
P <sub>0</sub>	Sprocket Hole Pitch	4.0 ± 0.1	
D <sub>0</sub>	Sprocket Hole Diameter	1.55 ± 0.05	
E	Sprocket Hole Location	1.75 ± 0.10	
F	Pocket Location	11.5 ± 0.1	
P <sub>2</sub>		2.0 ± 0.1	
Р	Pocket Pitch	16.0 ± 0.1	
A <sub>0</sub>	Pocket Dimensions	12.80 ± 0.1	
B <sub>0</sub>		10.35 ± 0.1	
K <sub>0</sub>		5.7 ±0.1	
W <sub>1</sub>	Cover Tape Width	21.0 ± 0.1	
d	Cover Tape Thickness	0.1 max	
	Max. Component Rotation or Tilt	10°	
R	Min. Bending Radius	30	

1.500 4 <u>Ø1.00</u> (TYP) 6 35-6 86 5 8 9.40-9.91 1.14-1.78 3.68-3.94 5.08 Max



# FAIRCHILD

NOTES:

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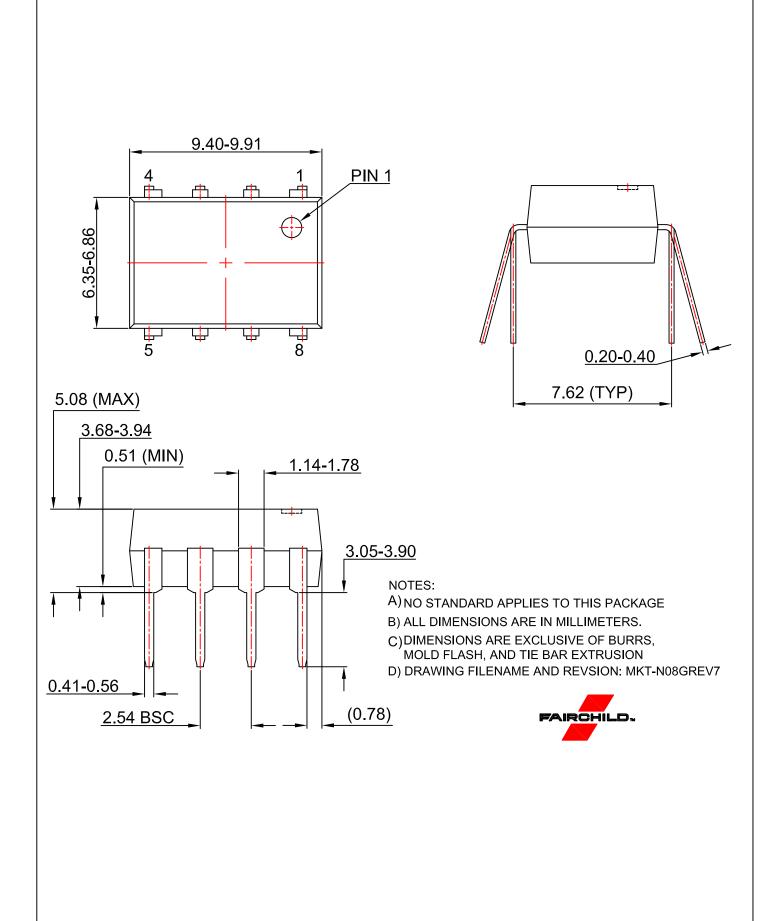
A) NO STANDARD APPLIES TO THIS PACKAGE

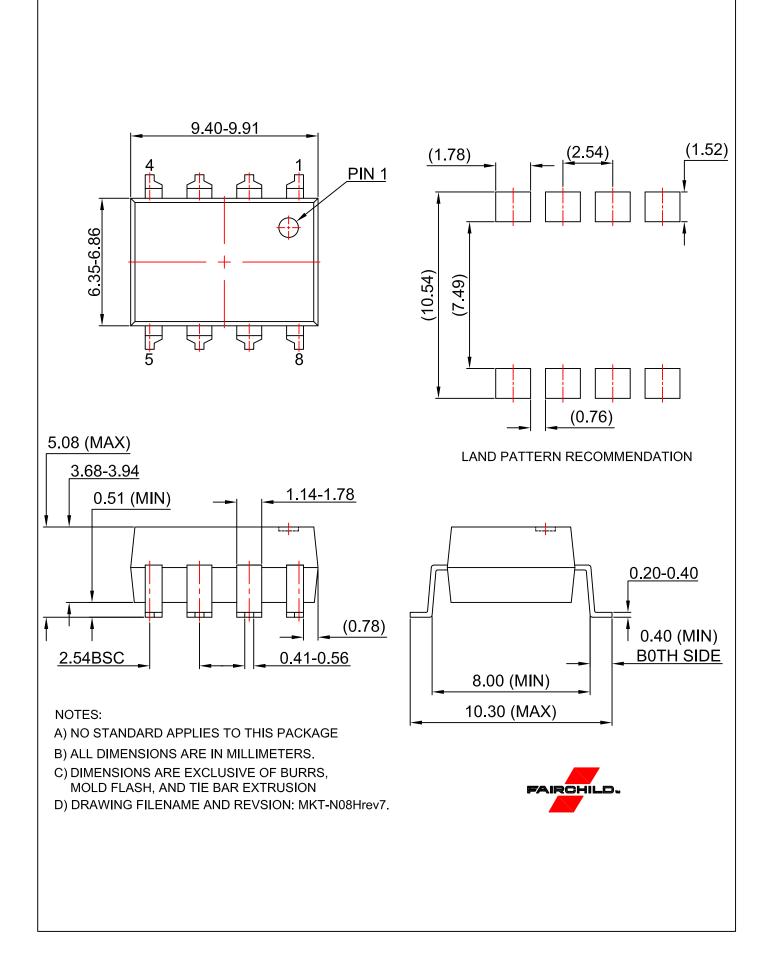
2.54 (Typ)

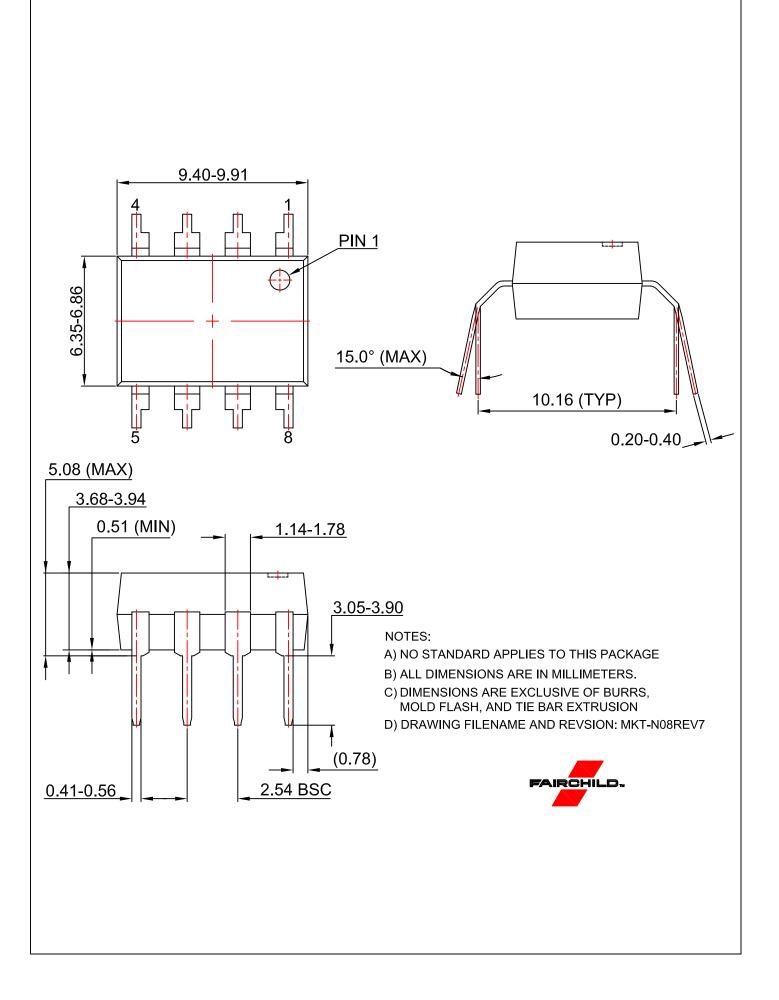
0.510(Min)

B) ALL DIMENSIONS ARE IN MILLIMETERS.

C) DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIOND) DWG FILENAME AND REVISION: MKT-N08Lrev2.









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Definition of Terms					
Datasheet Identification	Product Status	Definition			
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.			
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.			
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